

N-Channel 100 V (D-S) Power MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(m\Omega)(Typ.)$				
100	8.2 at V _{GS} = 10 V	100 ^a			

FEATURES

- DT-Trench II Power MOSFET
- 100 % Rg and UIS tested
- Fast switching

COMPLIANT

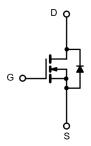
APPLICATIONS

- Load Switch
- · LED applications
- Networking

TO-263 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V _{DS}	100	V				
Gate-Source Voltage	V_{GS}	± 20					
Continuous Drain Courant /T = 175 °C\	T _C = 25 °C	1	100 ^a	A			
Continuous Drain Current (T _J = 175 °C)	T _C = 100 °C	l _D	48 ^a				
Pulsed Drain Current	I _{DM}	300	Α				
Avalanche Current ^b	I _{AR}	55					
Repetitive Avalanche Energy ^b	L = 0.1 mH	E _{AR}	115	mJ			
Maximum Power Dissipation ^b	T _C = 25 °C	D	138 ^c	· W			
	T _A = 25 °C	P _D	2.05				
Operating Junction and Storage Temperate	T _J , T _{stg}	- 55 to 175	°C				

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Limit	Unit				
Junction-to-Ambient	PCB Mount (TO-263) ^d	R _{thJA}	60	°C/W			
Junction-to-Case (Drain)		R _{thJC}	1.5	J 0/VV			

Notes:

- a. Package limited.
- b. Duty cycle ≤ 1 %.
- c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).

Rev. A 1



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = 250 μA	100			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaria Dirain Current	1	V _{DS} = 100 V, V _{GS} = 0 V			1	^	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 85 °C	10			μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α	
Drain-Source On-State Resistance ^a	Roor v	V _{GS} = 10 V, I _D = 20 A		8.2	10	mΩ	
Diani-Source On-State Nesistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 20 A		9.5	13		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		65		S	
Dynamic ^b							
Input Capacitance	C _{iss}			2158		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$		897			
Reverse Transfer Capacitance	C _{rss}			22			
Total Gate Charge ^c	Q_g			32			
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		3.7		nC	
Gate-Drain Charge ^c	Q _{gd}			1.2		1	
Gate Resistance	R _g		3.5			Ω	
Turn-On Delay Time ^c	t _{d(on)}			12			
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 0.6 \Omega$		8		- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D = 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		25			
Fall Time ^c	t _f			5			
Source-Drain Diode Ratings and Cha	aracteristics ⁻	Г _С = 25 °С ^b					
Continuous Current	Is				100	Α	
Pulsed Current	I _{SM}				300		
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	I _F = 1 A, V _{GS} = 0 V 0.6 1.0		1.0	V	
Reverse Recovery Time	t _{rr}			30		ns	
Reverse Recovery Charge	Q _{rr}	I _F = 20 A, dl/dt = 100 A/μs		190		nC	

Notes:

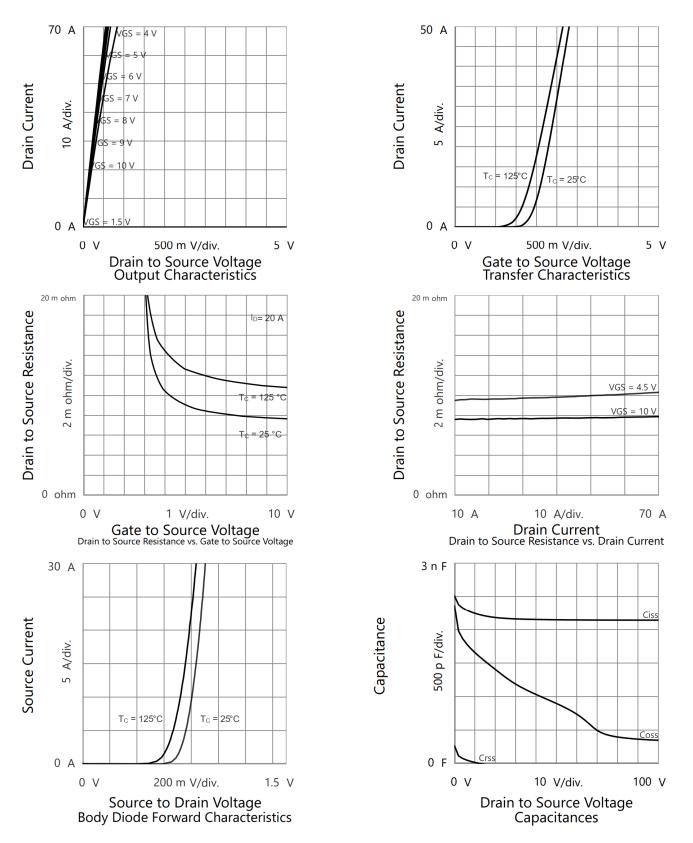
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



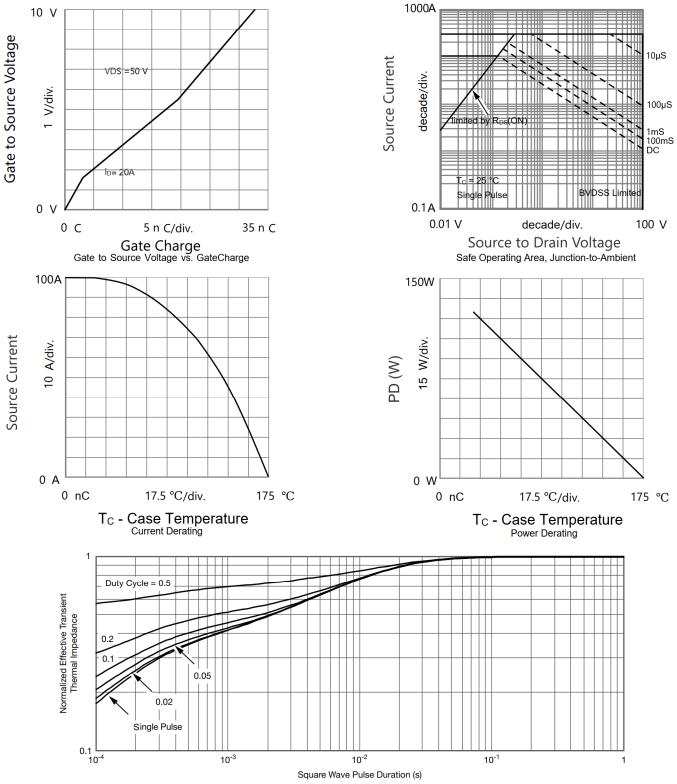


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





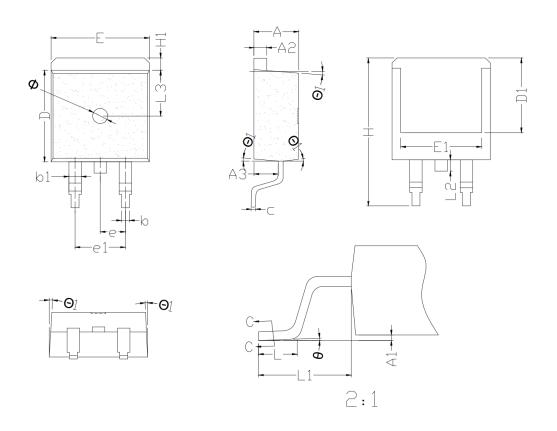
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case



TO-263 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
Α	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1		7.50REF		ф	0°	2°	5°
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ		1.5BSC	



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